Photochemical fabrication of three-dimensional micro- and nano-structured surfaces from a C_{60} monoadduct

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Exposure of Langmuir–Blodgett (LB) films of a C_{60} adduct supported on silicon wafers to UV light leads to cross-linking of the C_{60} moieties, which are resistant to removal by solvent exposure, whereas unexposed moieties are readily removed. This process provides a convenient and simple route for the fabrication of highly conjugated surface-attached structures, with dimensions ranging from micrometres (using masks) to a few tens of nanometres using light emitted from a scanning near-field optical microscope (SNOM). The SNOM writing velocity was found to significantly affect the lateral resolution and the height of the three-dimensional nanostructures. Increasing the writing velocity from 0.3 to 2 μ m s⁻¹ resulted in a decrease in the width of the structures from 240 nm to 70 nm (corresponding to the SNOM aperture diameter), respectively, and a reduction in the height from 8 nm (the thickness of the original film) to 3 nm, respectively. This approach provides a simple, direct route to surface-bound nanometre scale assemblies of C_{60} .

1 Introduction

Light is an attractive tool for the fabrication of structures and devices because of the paradigmatic status of photolithography in semiconductor device fabrication and the availability of a large toolkit of synthetic photochemical methodologies. The principal problem associated with the application of photochemical methods of fabrication has previously been thought to be the dominance of the diffraction effects as the Rayleigh limit is approached. Recently, however, the application of novel optical phenomena has opened up exciting prospects for photochemical modification of materials with a resolution significantly superior to that of conventional approaches. These include the exploitation of interferometric methods^{1–3} and of plasmonic phenomena,^{4–7} which are currently attracting rapidly growing interest.

One successful approach to the fabrication of nanostructures has been the exploitation of the near-field optical methods. Using a scanning near-field optical microscope (SNOM) coupled to a UV laser, self-assembled monolayers have been patterned and used as templates for the etching of structures in gold films with a resolution that may be as good as 9 nm, nearly $\lambda/30$.⁸⁻¹² This approach, which we have termed scanning near-field photolithography (SNP) provides a significant advance in photolithographic capability. Previously, however, it has predominantly been applied to the patterning of alkanethiol systems. Recently we have begun to explore its application to other types of photoactive materials, including monolayers of alkylsilanes.¹³ Recently, we reported a simple route to the fabrication of metal nanowires by utilizing near-field exposure of gold nanoparticles.¹⁴ Langmuir–Schaeffer films (bilayers) of thiol-stabilized gold nanoparticles were formed on silicon substrates and selectively exposed to UV light from a near-field probe. The result was the coagulation of the nanoparticles to form wires *ca.* 60 nm in width. Here we report a new route to the fabrication of C₆₀ structures that utilises a similar simple methodology. Synthetic modification of the C₆₀ molecules renders them readily amenable to Langmuir–Blodgett film formation¹⁵ and the photochemical cross-linking yields robust structures in a single step.

Since C₆₀, or buckminsterfullerene, was first discovered by Kroto et al.16 in 1985, fullerenes have received a great deal of attention because of the unique properties of their extended π -systems, giving rise to potential applications in the biological,17 electrical18 and chemical19 sciences. In 1991, Rao et al.²⁰ reported for the first time that C₆₀ was photosensitive. It was observed that after exposure to UV light, a C₆₀ film became insoluble in toluene. Evidence from laser desorption mass spectroscopy, infrared spectroscopy, Raman spectroscopy and optical absorption spectroscopy gave strong indications that the C₆₀ had polymerised and the C₆₀ clusters had not been destroyed during the UV light exposure. In addition, X-ray diffraction showed that the films became more disordered after the UV light exposure and the lattice had contracted. Initially, it was thought²⁰ that a $2\pi s + 2\pi s$ photochemical cycloaddition reaction was causing the cross-linking. However, the contraction seen between neighbouring C60 molecules was smaller than expected, and it was then proposed²⁰ that an =C=C= allenetype bridge may have been formed between the C₆₀ moieties to form C₆₀=C=C=C₅₈. After further spectroscopic studies

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performed by members of the same group²¹ and theoretical calculations made by Menon *et al.*,²² the formation of the allene-type bridge was ruled out and $2\pi s + 2\pi s$ photochemical cycloaddition was proposed as the most likely mechanism, whereby two σ -bonds are formed between two adjacent C₆₀ cages leading to the formation of a 4-membered ring. Later experimental studies²³⁻²⁵ and theoretical calculations^{24,26,27} concur with the mechanism being $2\pi s + 2\pi s$ photochemical cycloaddition. The polymerisation is thought to be initiated by the dimerisation between two adjacent C₆₀ cages followed by further $2\pi s + 2\pi s$ cycloadditions to form longer oligomers.^{24,25} Often, it has been observed that there are a number of oligmers formed with the dimer being the most abundant.^{20,24,27} The



Fig. 1 The C_{60} adduct and a schematic diagram (right) showing the patterning methodology.

distribution of the oligomers formed is affected by temperature at which the polymerisation is performed.^{24,25}

The effect of electron beam irradiation on C_{60} is remarkably different. Although electron beam irradiation renders C_{60} and its methanofullerene derivatives insoluble in toluene compared to unirradiated regions,^{28–32} it is also well documented that the electron beam irradiation leads to extensive cage fragmentation and the formation of disordered networks of graphite-like particles.³⁰ In fact, the methanofullerene derivatives have been shown to have potential as negative tone resists for electron beam lithography and they are achieving better sensitivity than some of the commercially available polymers such as poly(methyl-methacrylate) (PMMA).³²

The clear advantage of a photolithographic patterning process would thus be that it offers the possibility of cross-linking C_{60} while causing minimal modification to its molecular structure. The drawback has previously been the limited resolution associated with photopatterning techniques. Here we demonstrate that by using near-field methods it is possible to realise exceptional resolution during the photochemical fabrication of C_{60} nanostructures.

The process used in the present study is illustrated in Fig. 1. Langmuir films of the amphiphilic C_{60} adduct were transferred on to the Si/SiO₂ substrate *via* the Langmuir–Blodgett (LB) technique, followed by irradiation with UV light (244 nm) either in a parallel fashion through a mask or serially with the SNOM. The irradiation induces the cross-linking in the C_{60} moieties rendering the irradiated areas insoluble, such that the unirradiated areas of the C_{60} adduct film may easily be removed by rinsing with chloroform leaving the insoluble irradiated C_{60} film intact.

2 Results and discussions

The synthesis of the C_{60} adduct is shown in Scheme 1. The derivatisation was achieved by the reaction of 3,4-dihydro-3'*H*-pyran (THP) with tetraethylene glycol (1) in the presence of



Scheme 1 Synthesis of the C_{60} adduct.

p-toluenesulfonic acid monohydrate. The resultant monosubstituted tetrahydropyranyl ethylene glycol (2) was esterified with malonyl dichloride in the presence of pyridine, affording the bis-ester (3). The cyclopropyl fullerene bis-ester (4) was synthesized *via* the Bingel reaction³³ between the bis-ester (3) and C_{60} in the presence of base and iodine in the dark. The THP moieties were removed by TFAA to afford the C_{60} adduct.

The Π -A isotherms for the compression (10 cm² min⁻¹) and decompression (10 cm² min⁻¹) of the C₆₀ adduct Langmuir film are shown in Fig. 2. Three cycles are shown. The liquid expanded phase (LE) in cycle 1 persists to just below 1 nm². This value is in good agreement with the molecular area of the C₆₀ (0.75 nm²). The surface pressure rises rapidly to ~20 mN m⁻¹ at an area per molecule of 0.5 nm², at which point a kink in the curve appears. After the kink the rate of increase in surface pressure decreases, which suggests possible shearing of the film forming a partial bilayer. Decompression and recompression (cycles 2 and 3) reveal that the onset of pressure from the liquid expanded (LE) phase occurs at increasingly smaller areas per molecule indicating aggregation and/or bilayer structures.³⁴⁻³⁶

The C_{60} adduct Langmuir films were transferred to the substrate at a fixed surface pressure of 30 mN m⁻¹, and a dipping velocity of 5 mm min⁻¹. Samples were prepared by transferring two/three bilayers using Langmuir–Blodgett deposition techniques. The resulting film structures were characterised by tapping mode atomic force microscopy (AFM). A representative image is shown in Fig. 3a. The surface is uniformly covered with the C_{60} adduct, and there is no evidence of any defects. The topography of the films did not change over 3 days suggesting that they remained stable over this period. The thicknesses of the films were determined by measuring the step height between



Fig. 2 Π -A Isotherm of the C₆₀ adduct.



Fig. 3 AFM images of the C_{60} adduct films (a) before and (b) after exposure to UV light for 1 min, and (c) after rinsing with CHCl₃. Image sizes: (a), (b) are 20 \times 20 μm^2 , and (c) is 100 \times 100 μm^2 .

the covered and uncovered regions of the substrate, and were found to be 8 and 12 nm, which are consistent with two and three bilayers of the C_{60} adduct, respectively.

To investigate whether the C_{60} adduct films were photosensitive and stable after UV light irradiation, films consisting of three bilayers were exposed to UV light through a Cu TEM grid ($\lambda =$ 244 nm) for 1 min. Fig. 3a shows an AFM image of the film before irradiation and Fig. 3b after irradiation. It is clear that there has been no change in the film topography. However, after rinsing with CHCl₃ the masked areas of the film were removed, while the film exposed to UV light remained on the surface (Fig. 3c). Well-defined square islands with lateral dimensions equal to the width of the mask features and a vertical dimension of ~12 nm were observed.

Nanoscale patterns were fabricated by exposing the films of the C_{60} adduct with UV light from a near-field probe. Two bilayers were deposited on a hydrophobic silicon substrate. After exposure, the films were rinsed with CHCl₃. Again, the resulting cross-linked structures were found to be stable, while the unexposed material was easily removed. A variety of writing rates were used to examine whether there was an influence on the resulting feature size. Fig. 4 shows the AFM images of the samples patterned at SNOM scan velocities of 0.3, 1 and 2 µm s⁻¹. All the images show that well-defined, continuous structures, which are free from defects, have been formed, with the line thickness varying with the writing rate. Lines formed with writing velocities of 0.3, 1 and 2 µm s⁻¹ exhibited full widths at



Fig. 4 Representative AFM images and cross-section analysis for the nanostructures formed after writing onto 2 bilayers of the C_{60} adduct LB films with SNOM writing velocities of (a) 0.3 µm s⁻¹, (b) 1 µm s⁻¹, (c) 2 µm s⁻¹ and rinsing the films with CHCl₃.

half maximum height (FWHM) of ~240, ~100, ~70 nm, respectively. The line lateral thickness observed with writing velocity of 2 μ m s⁻¹ is comparative to the diameter of the aperture of the SNOM probe (~70 nm), and hence indicates that the polymerisation of the film has not spread outside the area illuminated by the probe, whereas, at the slower velocities, 0.3 and 1 μ m s⁻¹, some polymerisation has extended laterally through the film. It is known that the electric field associated with a near-field excitation diverges reasonably rapidly through a dielectric medium, and the most likely explanation for the observation of structures larger than the aperture diameter here is the effective spreading of the excitation through the finite depth of the resist medium (*ca.* 8 nm for two bilayers of C₆₀ adduct). Nevertheless, the resolutions exhibited by the structures in Fig. 4 are extremely good.

The height of the structures formed with writing velocity of 0.3, 1 and 2 μ m s⁻¹ are observed as ~8, ~3 and ~3 nm, respectively. The height of the structure obtained with writing velocity of 0.3 μ m s⁻¹ is comparable to the C₆₀ adduct LB film (~8 nm, determined from AFM), whereas at the faster velocities the structures are less than half of the initial LB film thickness (before irradiation). This observation suggests that incomplete polymerisation occurs at faster writing times (*i.e.* lower dwell times), and the C₆₀ adducts are not fully polymerised and may be rinsed away.

In some images, narrow, discontinuous lines may be observed that extend diagonally between the main features created lithographically. These are thought to be artifacts resulting from the minimal exposure of the samples as the probe moved rapidly (35 μ m s⁻¹) from the end of one line to the beginning of the next structure to be written. It appears even at this much reduced exposure the C₆₀ adduct film is still partially polymerised, leading to even thinner (but incomplete) lines.

3 Conclusion

In summary, it is clear that near-field optical methods provide a simple route to the fabrication of surface-bound nanostructures composed of C₆₀ building blocks. This methodology may have widespread utility in the fabrication of functional molecular nanostructures. The relatively small perturbation of the molecular structure of the C_{60} molecular via (i) the attachment of the hydrophilic glycol chain in the formation of the C_{60} adduct, and (ii) the subsequent photochemical cross-linking in the LB films, coupled to the small inter C₆₀ moiety separation in the nanowires lends itself to the exciting possibility that these nanowires may very well be electrically conductive as a result of overlap of the π -frameworks from neighbouring molecules. Currently we are examining this aspect further. The integration of novel nanolithographic methodologies that can induce specific chemical reactions in nanomaterials presents a new paradigm for the fabrication of nanostructured surfaces with threedimensional form and potential function.

4 Experimental

4.1 Chemicals

Unless otherwise stated, all commercially available chemicals were purchased from Aldrich and were used as received. C_{60}

was purchased from the Mer Corporation and was used as received. Solvents were either used as received or dried; DCM from CaH₂, THF and PhMe were distilled from Na–benzophenone ketyl under a N₂ atmosphere. Thin-layer chromatography (TLC) was carried out on aluminium plates coated with silica gel 60 F254 (Merck 5554). The TLC plates were air-dried and analysed under a short wave UV lamp (254 nm) or by developing the TLC plates in an I₂ chamber. Column chromatography separations were performed on silica gel 120 (ICN Chrom 32–63, 60 Å).

4.2 Synthesis of C₆₀ adduct

2-(2-{2-[2-(Tetrahydropyran-2-yloxy)ethoxy]ethoxy}ethoxy)ethanol (2). A solution of 3, 4-dihydro-2H-pyran (3.27 ml, 35.9 mmol) in dry DCM (50 ml) was added dropwise to a stirred, ice cold solution of tetraethylene glycol (1) (18.6 ml, 107.7 mmol) and p-toluenesulfonic acid monohydrate (0.137 g, 0.719 mmol) in dry DCM (500 ml) under a N₂ atmosphere. The solution was allowed to warm to room temperature and was stirred overnight. The DCM was removed in vacuo and the resulting oil purified by flash column chromatography (eluent; EtOAchexane-MeOH, 8:1:1). The solvent was removed in vacuo to afford a pale yellow oil (6.98 g, 71%). v_{max}/cm⁻¹ (film): 3491 m,br (O-H), 2940 m (C-H), 2871 m (C-H), 1119 m (THP, C-O-C), 1072 (C-O-C); δ_H (300 MHz; CDCl₃; Me₄Si) 4.57-4.60 (1 H, br, m, THP), 3.77-3.86 (2 H, br, m, THP), 3.42-3.51 (1 H, br, m, THP), 3.54-3.72 (15 H, br, m, HO(CH₂CH₂O)₃CH₂-, *THP*), 2.82 (1 H, br, s, -OH), 1.45–1.85 (6 H, br, m, *THP*); $\delta_{\rm C}$ (75 MHz; CDCl₃; Me₄Si) 98.8, 77.7, 73.1, 70.8, 70.7, 70.2, 66.9, 62.4, 61.8, 30.8, 30.7, 25.6, 19.7; m/z (ESMS): 301 ([M + Na]⁺, 100%); m/z (HRMS): found 301.1617. Calc. mass for C13H26O6Na: 301.1627.

Malonic acid bis-2-(2-{2-[2-(tetrahydropyran-2-yloxy)ethoxy]ethoxy{ethoxy) ester (3). A solution of malonyl dichloride (0.70 ml, 7.19 mmol) in dry DCM (30 ml) was added dropwise to a stirred, ice cold solution of tetrahydropyranyl ether (2) (4.00 g, 14.40 mmol) and dry pyridine (1.45 ml, 18.00 mmol) in dry DCM (150 ml) under a N₂ atmosphere. The dark red coloured reaction mixture was allowed to warm to room temperature and stirred overnight. Followed by plug filtration (silica gel) washing first with DCM (200 ml) and secondly with EtOAc (300 ml) to elute the product. The EtOAc was removed in vacuo and the crude oil purified by flash chromatography (gradient elution: 70 to 100% EtOAc in hexane, increasing in increments of 5% EtOAc per 100 ml of eluent). The solvent was removed in vacuo to yield a yellow oil (2.24 g, 50%). $\delta_{\rm H}$ (300 MHz; CDCl₃; Me₄Si) 4.58–4.63 (2 H, br, m, THP), 4.23– 4.28 (4 H, br, m, 2(-CH₂CH₂CO₂CH₂CH₂)), 3.78-3.89 (4 H, br, m, THP), 3.54-3.71 (26 H, br, m, (-CH₂O(CH₂CH₂O)₃₋ CH2O-), THP), 3.40-3.51 (4 H, br, m, -O2CCH2CO2-, THP), 1.41-1.85 (12 H, br, m, THP), δ_C (75 MHz; CDCl₃; Me₄Si) 166.5, 99.9, 71.7, 69.9, 67.7, 65.6, 63.2, 42.3, 31.6, 26.5, 20.5; m/z (ESMS): 647 ([M + Na]⁺, 100%); m/z (HRMS): calc. mass for C₂₉H₅₂O₁₄Na 647.3255, found 647.3245.

3'H-Cyclopropa[1,9][5,6]fullerene-C₆₀-I_h-3,3'-carboxylic-2-(2-{2-[2-(tetrahydropyran-2-yloxy)ethoxy]ethoxy} ester (4). A solution of 1,8-diazabicyclo(5.4.0)undec-7-ene (64 mg, 62.55 µmol) in dry PhMe (50 ml) was added dropwise to a stirred, ice cold solution of C₆₀ (300 mg, 417 µmol), iodine (53 mg, 209 µmol) and bis-tetramalonate ester (3) (130 mg, 208 µmol) in dry PhMe (100 ml). The reaction was covered with aluminium foil and stirred overnight at room temperature under a N₂ atmosphere. Followed by plug filtration (silica gel) washing first with PhMe (200 ml) to remove the excess C_{60} and secondly with 5% MeOH in DCM (200 ml) to elute the product. The solvent was removed from the second fraction in vacuo and purified by flash chromatography (gradient elution: 0 to 3% MeOH in DCM; increasing in increments of 0.5% MeOH per 100 ml of eluent). The solvent was removed to yield a dark brown tar (140 mg, 49%). v_{max}/cm⁻¹ (nujol): 2939 m (C-H), 2871s (C-H), 1119s (THP, C–O–C), 1072s (C–O–C); $\delta_{\rm H}$ (300 MHz; CDCl₃; Me₄Si) 4.58–4.63 (6 H, br, m, (-CH₂CO₂CH₂CO₂CH₂-), THP) 3.53-3.88 (30 H, br, m, $2(-CH_2O(CH_2CH_2O)_3CH_2O) +$ THP), 3.42-3.51 (2 H, br, m, THP), 1.42-1.84 (12 H, br, m, *THP*); δ_C (75 MHz; CDCl₃; Me₄Si) 163.5, 145.2, 145.1, 144.8, 143.1, 143.0, 142.9, 142.2, 141.8, 140.9, 139.0, 98.9, 70.6, 70.5, 68.7, 66.6, 62.2, 30.5, 25.4, 19.5; m/z (MALDI-TOF MS): 1368 $([M + 2H]^+, 35\%).$

H-Cyclopropa[1,9][5,6]fullerene-C₆₀-I_h-3,3'-carboxylic-2-(2-{2-[2-(tetrahydropyran-2-yloxy)ethoxy]ethoxy]ethoxy]alcohol (C₆₀ adduct). TFAA (113 mg, 538 µmol) was added dropwise at room temperature to a solution of 4 (75 mg, 55 µmol) in a 1 : 1 mixture of DCM-MeOH (7 ml) followed by heating the reaction mixture at 50 °C for 2 h. The reaction mixture was allowed to cool to room temperature and the solvent was removed in vacuo. The crude solid was purified by flash chromatography (gradient elution: 0 to 2% MeOH in DCM, increasing in increments of 0.5% per 100 ml of eluent) and solvent removed in vacuo to yield a brown solid (53 mg, 82%). HPLC run in 50% MeCN and 50% H₂O showed compound was 97% pure (retention time: 13 min). Elemental analysis found: C, 80.51%; H, 2.84%. Calc. for $C_{79}H_{34}O_{12}$: C, 80.75%; H, 2.92%; ν_{max}/cm^{-1} (DCM) 3458 m (O-H), 3054 m (C-H), 2923 m (C-H), 1746s (C=O), 1072s (C–O–C); $\delta_{\rm H}$ (300 MHz; CDCl₃; Me₄Si) 4.67–4.63 (4 H, br, m, (-CH₂CO₂CCO₂CH₂-)), 4.23-4.28 (4 H, br, m, 2(-CO₂CH₂CH₂)), 3.53-3.88 (24 H, br, m, 2(-CH₂O(CH₂CH₂O)₃ CH₂O–); δ_C (75 MHz; CDCl₃; Me₄Si) 163.5, 147.0, 146.9, 146.4, 146.3, 145.6, 144.8, 144.7, 143.9, 143.6, 142.7, 140.8, 75.2, 75.2, 73.3, 73.0, 71.5, 69.0, 64.4; m/z (ESMS): 1197 ([M + Na]⁺, 100%); m/z (HRMS): found 1197.1967. Calc. mass for C₇₉H₃₄O₁₂Na: 1197.1948.

4.3 Compound characterisation

4.3.1 NMR. ¹H nuclear magnetic resonance (NMR) spectra were recorded on a Bruker AC 300 (300.13 MHz) spectrometer. ¹³C NMR spectra were recorded on a Bruker AV 300 (75.5 MHz) using Pendant pulse sequences. All chemical shifts are quoted in ppm to higher frequency from Me₄Si using deuterated chloroform (CDCl₃) as the lock and the residual solvent as the internal standard. The coupling constants are expressed in Hertz (Hz) with multiplicities abbreviated as follows; s = singlet, d = doublet, dd = double doublet, t = triplet, q = quartet and m = multiplet.

4.3.2 Mass spectrometry (MS). Electron impact mass spectroscopy (EIMS) was performed on VG Prospec. Low and high resolution electrospray mass spectrometry was performed on a micromass time of flight (TOF) instrument using methanol as the mobile phase. The matrix assisted laser desorption ionization–time of flight mass spectroscopy (MALDI–TOF MS) was performed on a Bruker Biflex. The samples were prepared by mixing the dissolved compounds with a matrix (sinapinic acid) and then allowing the solvent to evaporate to leave crystals as the samples.

4.3.3 Infrared spectroscopy (IR). The IR spectra were recorded as thin solid films on NaCl discs or KBr discs using a Perkin Elmer 1600 FT-IR. The solids were mixed with nujol to form a paste that was spread between the NaCl discs to form a thin film.

4.3.4 Elemental analysis. Elemental analysis was carried out on a Carlo Erba EA 1110 (C H N) instrument.

4.3.5 High performance liquid chromatography (HPLC). HPLC were recorded on a Dionex Summit System with Chromeleon Software, using a Summit UVD 170s UV/vis multi-channel detector with analytical flow cell. The analytical HPLC runs were performed on a Luna (Phenomenex), C_{18} , 250 × 4.6 mm ID, with 10 µm pore size column using a gradient of MeCN–H₂O.

4.4 Surface pressure-area $(\Pi - A)$ isotherm studies

The Π -A isotherm studies were performed using a Nima 611 trough with Wilhelmy type balance. Prior to use, the trough was cleaned with CHCl₃, IPA and 3 times with 15 M Ω H₂O. The subphase used to form the Langmuir film was 15 M Ω H₂O. The C₆₀ adduct (2.4 mg) was dissolved in CHCl₃ (5 ml) and 50 µl of the prepared solution was spread over the H₂O subphase at room temperature. The CHCl₃ was allowed to evaporate for 10 min before the isotherm studies were performed. The surface pressure was increased by reducing the surface area *via* controlling the closure of the barrier at a rate of 10 cm² min⁻¹ from 200 to 20 cm² during the isotherm studies.

4.5 Preparation of the C₆₀ adduct Langmuir films

The Langmuir films were prepared using a Nima 611 trough. Prior to the use, the trough was cleaned with CHCl₃, IPA and 3 times with 15 M Ω H₂O. The solution of the C₆₀ adduct (50 μ L, 0.41 mM) in CHCl₃ was spread over the H₂O subphase, left for 10 min for the solvent to evaporate and compressed at a rate of 10 cm² min⁻¹.

4.6 Preparation of the C₆₀ adduct Langmuir–Blodgett film

The LB bilayer films were formed on hydrophobic Si/SiO_2 substrates. The substrates were cleaned prior to use by immersing in IPA, which was distilled before use. The Si/SiO_2 substrates were hydrophobised with hexamethyldisilazane by placing the substrates in a chamber containing hexamethyldisilazane ensuring that the meniscus of the silazane was just below the upper surface of the substrate. The substrates were left for 24 h in the chamber followed by sonication in CHCl₃, IPA and 15 MΩ

H₂O for 1 min each and dried with N₂ after each sonication. The hydrophobic Si/SiO₂ substrates were lowered into and raised from the Langmuir film ($\Pi = 30$ nN m⁻¹) at a velocity of 5 mm min⁻¹ to afford the 2 or 3 bilayer LB films. Finally the LBFs were dried with N₂.

4.7 Photopatterning

Photopatterning was conducted using light from a frequency doubled argon ion laser (Coherent FreD 300C, Coherent U.K., Ely), which emits at 244 nm. For micrometre-scale patterning, a square grid mask consisting of $40 \times 40 \ \mu\text{m}^2$ square openings separated by 20 μ m beams was positioned on the C₆₀ adduct LBF and the sample was irradiated with power of 100 mW. The irradiation time was 1 min, and the area of illumination was typically 0.2–0.4 cm². The surface was then rinsed thoroughly with CHCl₃ and dried with N₂. For the scanning near-field photolithography, the laser was coupled to a Thermo-Microscopes Aurora III near-field scanning optical microscope fitted with a fused silica fiber probe (Veeco). The aperture diameter of the SNOM tip was ~70 nm. 16 lines were written for each probe velocity. The irradiated samples were rinsed thoroughly with CHCl₃ and dried with N₂.

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